

Product features

High precision machining technology

Low temperature drift, high power.

Ceramic substrate, 50 Ω coplanar waveguide

Gold wire bonding

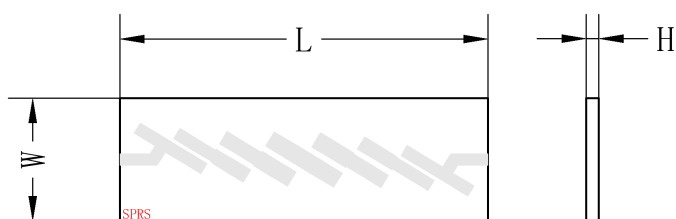
Tech specifications

Items	Parameters	Units
Center Frequency	26.0	GHz
Bandwidth	23.8-27.2	GHz
Center loss	2.3	dB
Ripple	1.0	dB
VSWR	1.7:1	
Group delay ripple	0.4	ns
Rejection	40@DC-20.8GHz	dBc
Rejection	40@30.2-40.0GHz	dBc

Other requirement (Design assurance)

power	2W CW
Operation Temp.	-55~+85°C
Storage Temp.	-55~+125°C
Outline size	L: 7.5, W: 2.5, h: 0.26

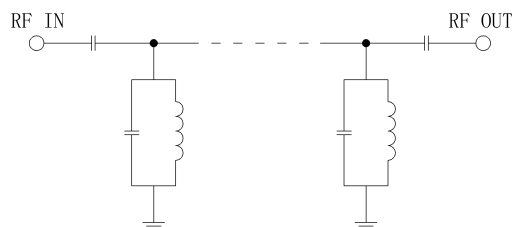
Outline drawing: Port centered



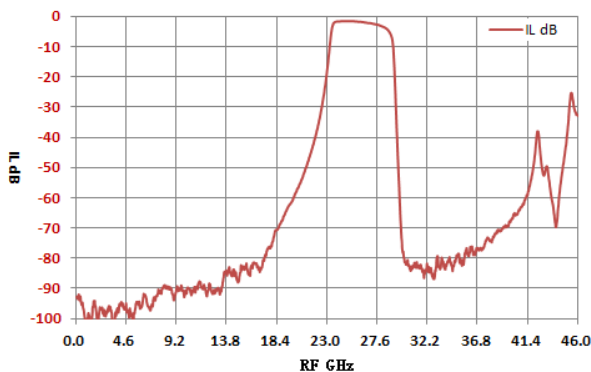
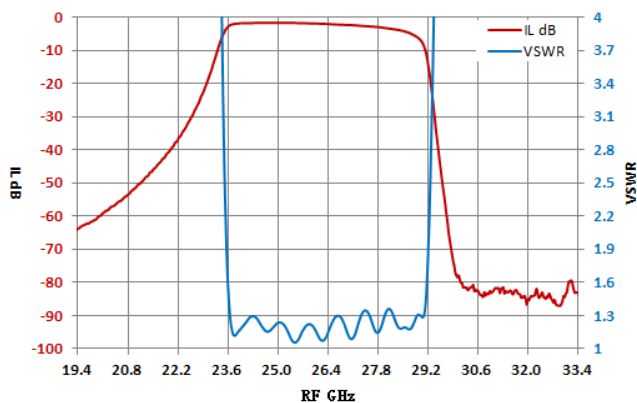
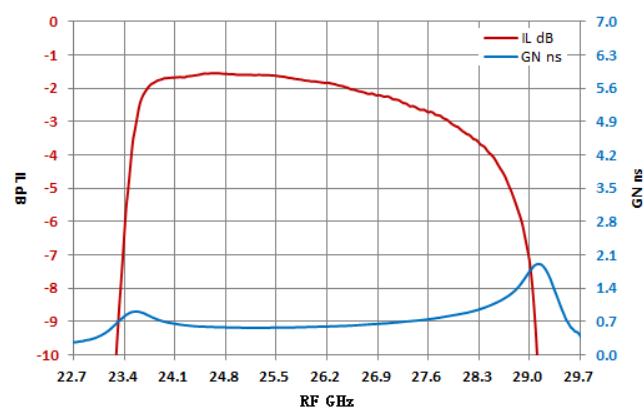
Reference picture



Schematic diagram

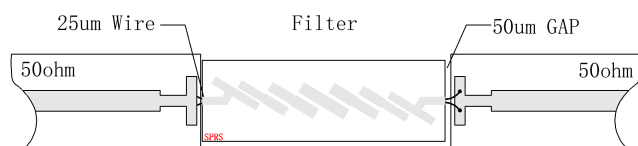


Typical test curve



Note: The specifications and performance data contained in this data sheet are based on tests established by CMW.

Suggested PCB Layout



PCB Rogers5880, h: 0.254mm	PCB Rogers4350B, h: 0.254mm
	

Note

- 1: 0.1mm from the side wall, 1.75mm from the surface to the upper cover.
- 2: Suggest using conductive adhesive for bonding;
- 3: The chip should be installed on kovar alloy or molybdenum copper;
- 4: Suggest using a T-shaped structure for microstrip bonding.